# Overview of Simulation Strategies for Nanoelectronics

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## Outline

- $\Rightarrow$  Introduction to Nanoelectronics
- $\Rightarrow$  Nanoelectronics in ITRS
- $\Rightarrow$  Molecular Simulation
- $\Rightarrow$  Conclusion



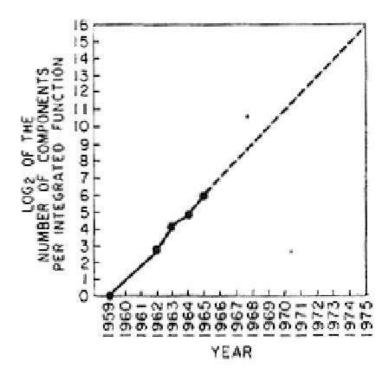
#### Introduction

## Moore's Law

- $\Rightarrow$  Exponential growth.
- ⇒ Cost per function reduction:
  - $\rightarrow$  25-29% per year.
- $\Rightarrow$  Market growth:
  - $\rightarrow$  On average 17% per year.
- $\Rightarrow \quad \text{The law holds for about 45} \\ \text{years.}$
- $\Rightarrow$  ITRS
  - → Industry want to keep with this law further.

Gordon E. Moore, 1965

Cramming more components onto integrated circuits





#### Introduction

## **Papers on Nanoelectronics: Web of Science**

- $\Rightarrow$  925 papers:
  - $\rightarrow$  Refereed journals.
- $\Rightarrow$  Search includes:
  - $\rightarrow$  Title,
  - $\rightarrow$  Keywords,
  - $\rightarrow$  Abstract.

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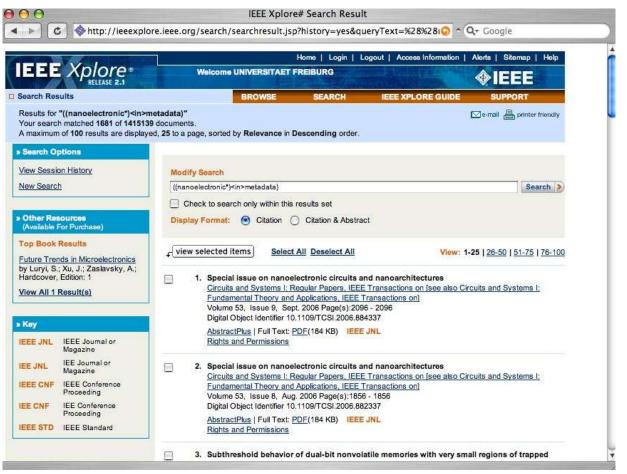
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#### Introduction

## **Papers on Nanoelectronis: IEEE**

- $\Rightarrow$  1681 papers.
- ⇒ Only IEEE publications.
- ⇒ IEEE conferences are included.





#### Introduction

#### **CRC On-Line Book Chapters**

 $\Rightarrow$  163 Hits

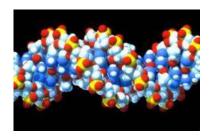
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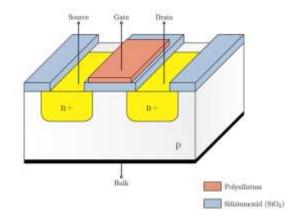


#### Introduction

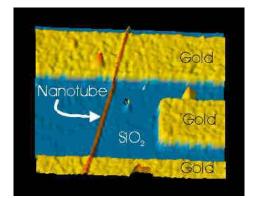
## What is Nanoelectronics?

- ⇒ Electronics on a nanometer scale (feature size less than 100 nm)
- $\Rightarrow$  Si-based (CMOS) and beyond-CMOS
- $\Rightarrow$  Is "electro" important?
  - $\rightarrow$  Information processing





Carbon nanotube transistor





## **ITRS 2005**

What technical capabilities need to be developed for the industry to stay on Moore's Law and the other trends?

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## Contributors

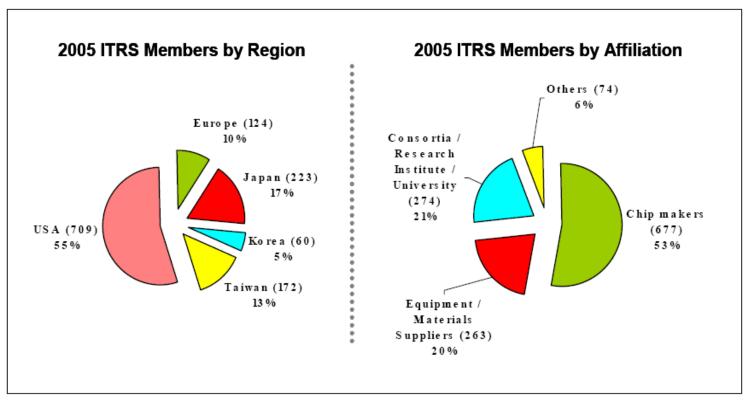


Figure 1 Composition of the ITRS Teams—1288 Global Participants





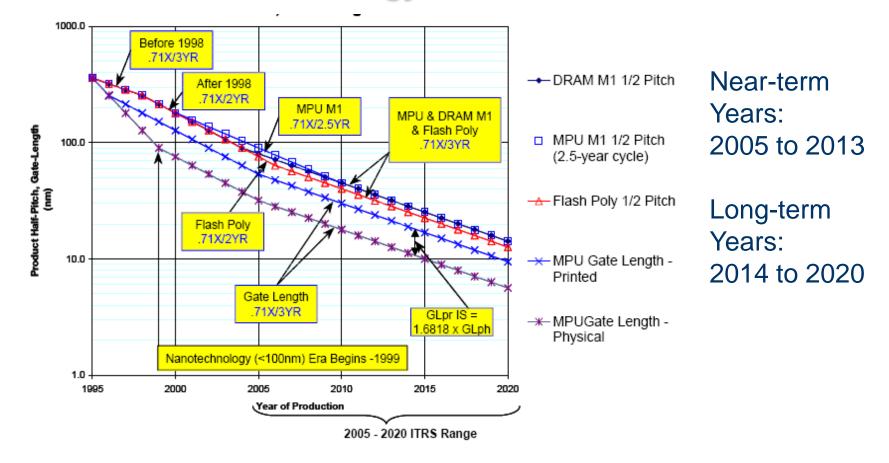
## Structure

- $\Rightarrow$  Executive Summary (89 pages)
- ⇒ 11 Focus International Technology Working Groups
  - $\rightarrow$  ...
  - → Emerging Research Devices / Emerging Research Materials
  - $\rightarrow$  ...
- ⇒ 4 Crosscut International Technology Working Groups
  - $\rightarrow$  ...
  - $\rightarrow$  Modeling and Simulation





## **ITRS Product Technology Trend**





## Scaling CMOS

		~		1					
Year of Production	2005	2006	2007	2008	2009	2010	2011	2012	2013
DRAM ½ pitch (nm) (contacted)	80	70	65	57	50	45	40	36	32
DRAM and Flash									
DRAM ½ pitch (nm)	80	70	65	57	50	45	40	35	32
Flash ½ pitch (nm) (un-contacted poly)	76	64	57	51	45	40	36	32	28
Contact in resist (nm)	94	79	70	63	56	50	44	39	35
Contact after etch (nm)	85	72	64	57	51	45	40	36	32
Overlay [A] (3 sigma) (nm)	15	13	11	10	9	8	7.1	6.4	5.7
CD control (3 sigma) (nm) [B]	8.8	7.4	6.6	5.9	5.3	4.7	4.2	3.7	3.3

Table 76a Lithography Technology Requirements-Near-term Years

Manufacturable solutions exist, and are being optimized

Manufacturable solutions are known

Interim solutions are known

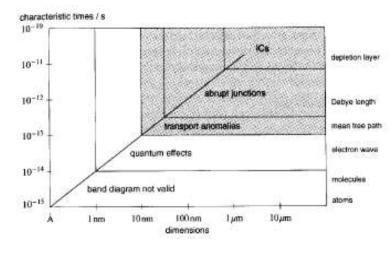
Manufacturable solutions are NOT known

٠		





- $\Rightarrow$  CMOS is the workhorse of the industry.
- ⇒ Yet, scaling of CMOS has technological and physical limits.
- ⇒ The semiconductor industry's future success continues to depend on new ideas.
- ⇒ Chapter on Emerging Research Devices including Emerging Research Materials.



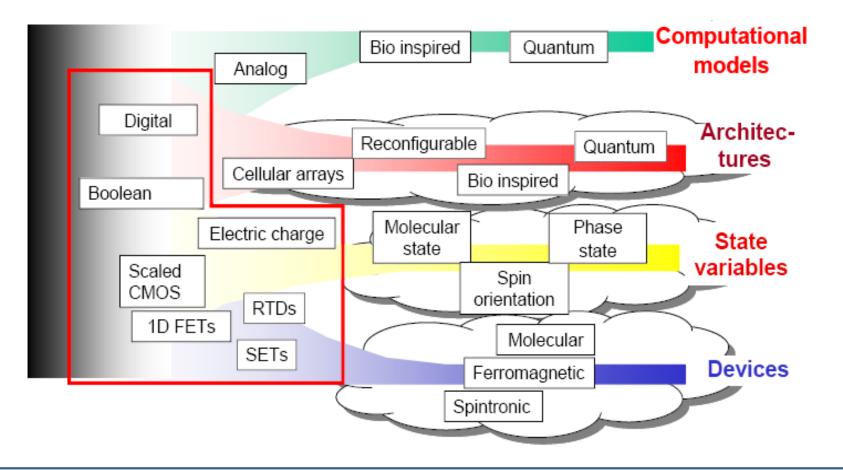
Goser Gloeserkoetter Dienstuhl



ITRS



## **Taxonomy for Nano Information Processing**







## **Devices and Architectures**

#### $\Rightarrow$ Devices:

- → Carbon nanotube and nanowires,
- $\rightarrow$  Ferroelectric FET memory,
- $\rightarrow$  Molecular,
- $\rightarrow \ \, \text{Nano floating gate} \\ \text{memory,}$
- $\rightarrow$  Polymer memory,
- $\rightarrow$  Polymer transistor,
- → Resonant tunneling devices,
- $\rightarrow$  Spin transistor.

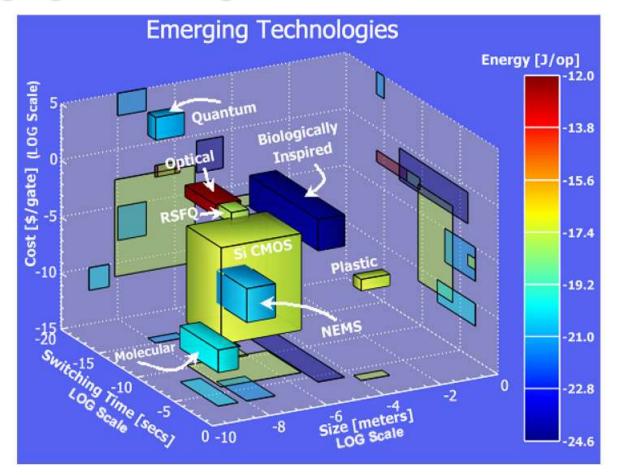
 $\Rightarrow$  Architectures:

- $\rightarrow$  Quantum Cellular Automata,
- → Cellular Nonlinear Networks,
- $\rightarrow$  Reconfigurable Implementations,
- → Biologically Inspired Implementation.





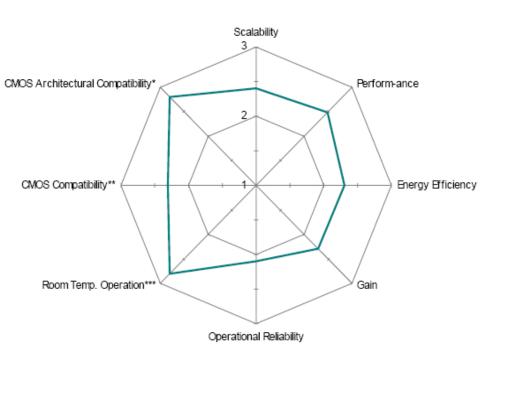
## **Emerging Technologies and CMOS**

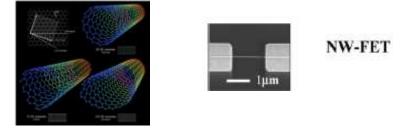






## **Potential Solutions for Logic Devices (CNT and NW)**





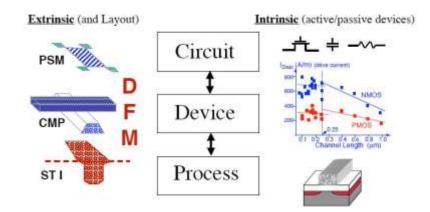
	Substantially exceeds CMOS
	<ul> <li>* or is compatible with CMOS architecture</li> </ul>
3	** or is monolithically integrable with CMOS wafer technology
	***or is compatible with CMOS operating temperature
	(i.e., Substantially Better than Silicon Logic)
	Comparable to CMOS
	* or can be integrated with CMOS architecture with some difficulty
2	** or is functionally integrable (easily) with CMOS wafer technology
	***or requires a modest cooling technology, $T \ge 77K$
	(i.e., Comparable to Silicon Logic)
	Substantially (2×) inferior to CMOS
1	* or can not be integrated with CMOS architecture
	** or is not integrable with CMOS wafer technology
	*** <i>or</i> requires very aggressive cooling technology, T < 77K
	(i.e., Substantially Worse that Silicon Logic)





## Modeling and Simulation: Technology CAD for CMOS

- ⇒ High-frequency device and circuit modeling
- $\Rightarrow$  Front-end process modeling
- ⇒ Integrated modeling of equipment and materials
- $\Rightarrow$  Lithography simulation
- ⇒ Thermo-mechanical-electrical modeling for interconnections and packages







## **Modeling and Simulation: Molecular Simulation**

- ⇒ Ultimate nanoscale CMOS simulation
- $\Rightarrow$  Nano-scale modeling of novel devices
- $\Rightarrow$  Modeling of new materials
- Nanoscale simulation capability including accurate atomistic and quantum effects

#### $\Rightarrow$ Algorithms:

- → Efficient atomistic/quantum models; ab-initio or molecular dynamics based topography simulations;
- → Multi-scale simulation (atomistic-continuum); fast coupling of equipment-topography-electrical-reliability models; hierarchichal full-chip simulation.



## **Model Order Reduction for EDA**

#### $\Rightarrow$ Current EU projects:

- → COMSON (COupled Multiscale Simulation and Optimization in Nanoelectronics) http://www.comson.org/
- → CHAMELEON RF, (Comprehensive High-Accuracy Modelling of ELectromagnetic Effects in Complete Nanoscale RF blocks) http://www.chameleonrf.org/



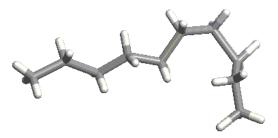
 → O-MOORE-NICE, (Operational MOdel Order REduction for Nanoscale IC Electronics)



#### **Molecular Simulation**

## **Course: Molecular Simulation for MST**

- $\Rightarrow$  J. G. Korvink, E. B. Rudnyi
  - $\rightarrow$  http://evgenii.rudnyi.ru/teaching.html#md
- $\Rightarrow$  Introductory course for MST engir
- $\Rightarrow$  12 lectures, 3 computational labs





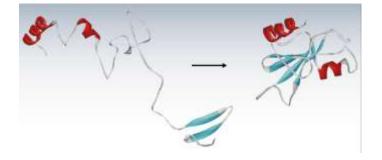




#### **Molecular Simulation**

## **From the First Principles**

- $\Rightarrow$  Ab initio (from the beginning)
- ⇒ Input: A few fundamental constants
  - → electron mass, proton mass, Plank constant, speed of light, ...
- $\Rightarrow$  Output: Everything
- $\Rightarrow$  Computationally expensive
- ⇒ Blue Gene: IBM Petaflop computer
  - $\rightarrow$  Protein folding







#### **Molecular Simulation**

## Hierarchy

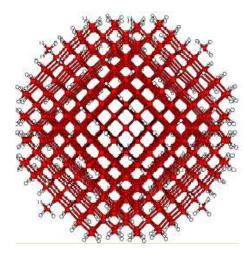
#### $\Rightarrow$ Potential Energy Surface (0 K)

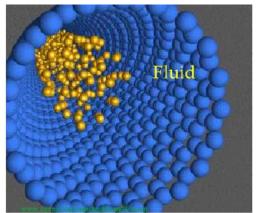
- → Electronic Schrödinder Equation
- → Semiempirical methods
- → Molecular Mechanics

#### $\Rightarrow$ Adding Entropy and Temperature

- → Molecular Dynamics
- $\rightarrow$  Monte Carlo

#### $\Rightarrow$ QSAR (empirical correlations)







at. # of n<sup>th</sup> nucleus

**Molecular Simulation** 

 $H\psi = E\psi$ 

Nuclei  $(\mathbf{R})$  and electrons  $(\mathbf{r})$ :

distance between

electrons i & J

**Schrödinger Equation**  $\Psi(\boldsymbol{R},\boldsymbol{r})$  $\mathbf{H} = \mathbf{T}_{nuc} + \mathbf{T}_{elec} + \mathbf{U}_{nuc-nuc} + \mathbf{U}_{elec-elec} + \mathbf{U}$ elec-nuc del operator for nuclei del operator for electron H = ass of electron mass of n<sup>th</sup> e nucleus distance Pairs Pairs 8 nucleus n of Nuclei of Elec.

distance between

nuclei n and m



#### **Molecular Simulation**

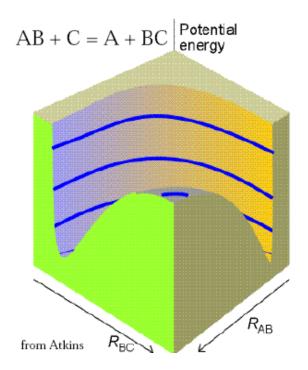
## **Potential Energy Surface**

- ⇒ Born-Oppenheimer Approximation
- $\Rightarrow$  Proton is 1836 times heavier than electron.
  - $\rightarrow$  Factorize for nuclei part

 $\Psi(\boldsymbol{R},\boldsymbol{r}) = \Psi(\boldsymbol{R})\psi(\boldsymbol{r};\boldsymbol{R})$ 

→ Schrödinger equation for electrons

 $H_{el}\psi(\boldsymbol{r};\boldsymbol{R})=E_{el}(\boldsymbol{R})\psi(\boldsymbol{r};\boldsymbol{R})$ 

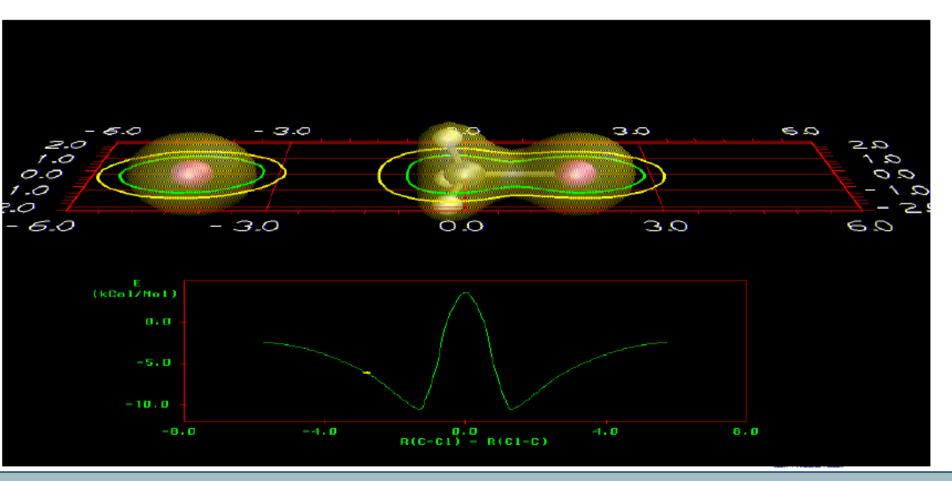




#### **Molecular Simulation**

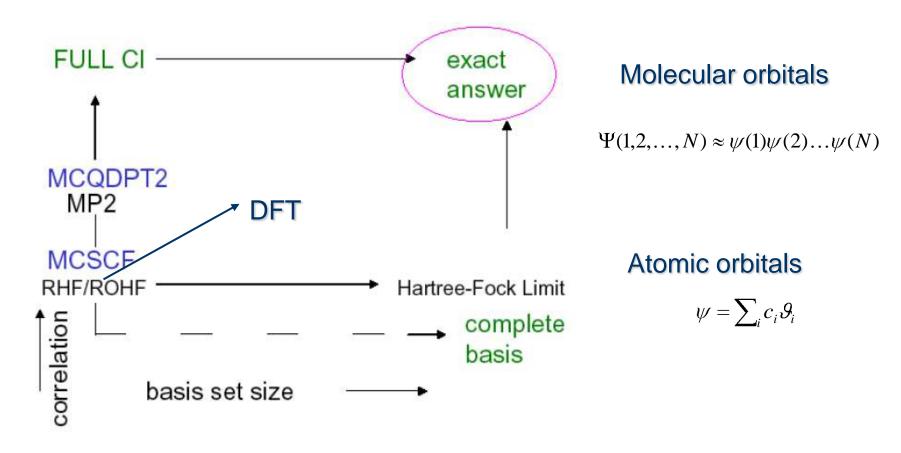
## **PES Example**

#### scsg9.unige.ch/fln/eng/toc.html





## **Quantum Chemistry Methods**

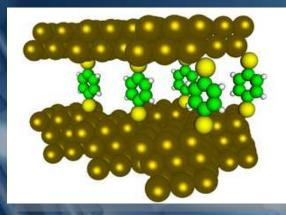


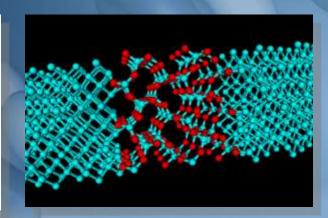


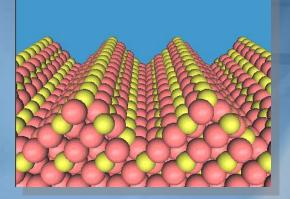
# What kind of software is needed?



As the main challenge in nanoscale technology derive from quantum phenomena across nanoscale junctions, interfaces and surfaces, it is critical to be able to accurately model such phenomena from quantum theory







Junctions

Interfaces

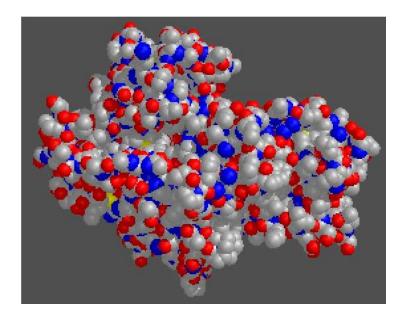
Surfaces

#### **Molecular Simulation**

## **Semiempirical Methods**

- $\Rightarrow$  Consider valence electrons only
- $\Rightarrow$  Neglect some integrals
- $\Rightarrow$  Parameterize the others

⇒ Accuracy depends on the parameterization



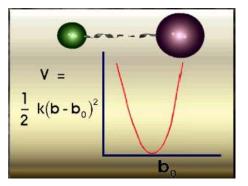


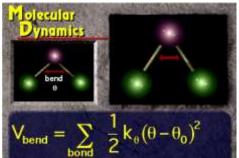
#### **Molecular Simulation**

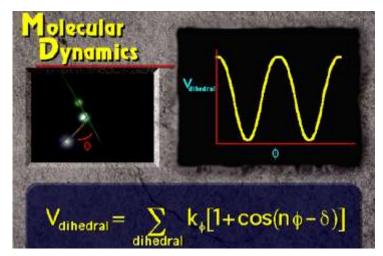
## **Molecular Mechanics**

#### $\Rightarrow$ Empirical force field

- → Bonding: streching, bending, torsion, crossterms;
- → Not-bonding: van der Vaals, electrostatic, hydrogen, etc...
- ⇒ Accuracy depends on the force field employed









#### **Molecular Simulation**

## **Molecular Dynamics and Monte Carlo**

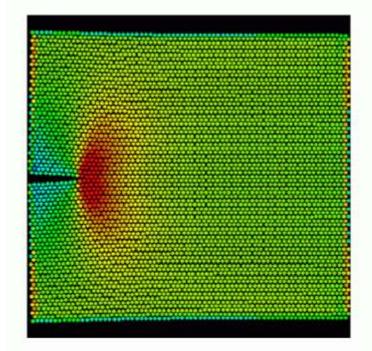
- $\Rightarrow$  Input:
  - $\rightarrow$  Potential energy surface
- $\Rightarrow$  Output:
  - $\rightarrow$  Heat conductivity, viscosity, ...

#### $\Rightarrow$ Time average

 $\rightarrow$  Integrating in time

#### $\Rightarrow$ Ensemble average

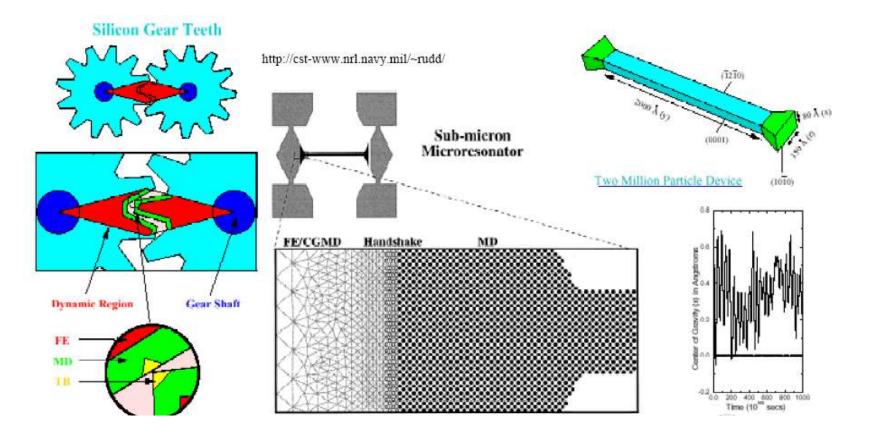
→ Sampling according to Bolztmann distribution





#### **Molecular Simulation**

## **Multiscale Simulation**





## Conclusion

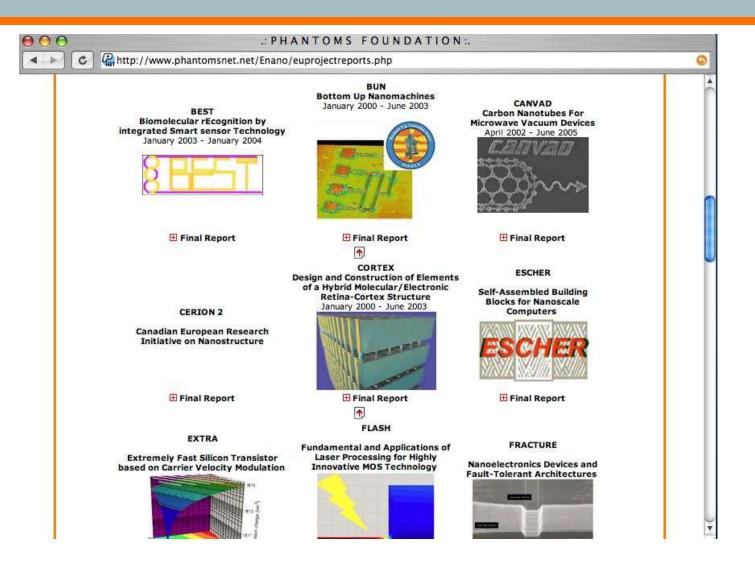
⇒ Beyond CMOS: New ideas for nanoelectronics

#### $\Rightarrow$ Molecular simulation is a natural way to check new ideas

#### $\Rightarrow$ Tight collaboration between industry and academia



#### **EU projects**









#### How to express your interest

You are invited to submit an Expression of Interest that should include a short overview of the organisation's activities in the nanoelectronics sector as well as the motivation for participating in ENIAC. A short CV of the person from the organisation that would be the contact point (including a web link) should also be included.

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#### **BMBF Nanotechnology**



## CADFEM

#### **BMBF Nanoelectronics**

